

Features

- Serial Peripheral Interface (SPI) Compatible
- Supports SPI Modes 0 (0,0) and 3 (1,1)
 - Datasheet Describes Mode 0 Operation
- Low-voltage and Standard-voltage Operation
 - 1.8 ($V_{CC} = 1.8V$ to 5.5V)
- 20 MHz Clock Rate (5V)
- 32-byte Page Mode
- Block Write Protection
 - Protect 1/4, 1/2, or Entire Array
- Write Protect (\overline{WP}) Pin and Write Disable Instructions for Both Hardware and Software Data Protection
- Self-timed Write Cycle (5 ms max)
- High Reliability
 - Endurance: One Million Write Cycles
 - Data Retention: 100 Years
- 8-lead JEDEC PDIP, 8-lead JEDEC SOIC, 8-lead Ultra Thin Mini-MAP (MLP 2x3), 8-lead TSSOP and 8-ball dBG2 Packages
- Die Sales: Wafer Form, Tape and Reel, and Bumped Wafers

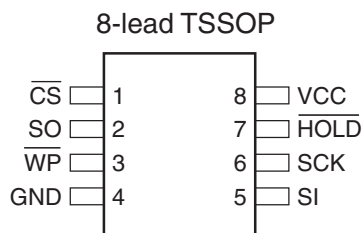
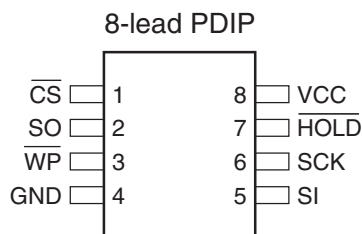
Description

The AT25080B/160B provides 8192/16384 bits of serial electrically-erasable programmable read-only memory (EEPROM) organized as 1024/2048 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The AT25080B/160B is available in space-saving 8-lead PDIP, 8-lead JEDEC SOIC, 8-lead Ultra Thin Mini-MAP (MLP 2x3) and 8-lead TSSOP packages.

The AT25080B/160B is enabled through the Chip Select pin (\overline{CS}) and accessed via a three-wire interface consisting of Serial Data Input (SI), Serial Data Output (SO), and Serial Clock (SCK). All programming cycles are completely self-timed, and no separate erase cycle is required before write.

Table 0-1. Pin Configuration

| Pin Name | Function |
|-------------------|-----------------------|
| \overline{CS} | Chip Select |
| SCK | Serial Data Clock |
| SI | Serial Data Input |
| SO | Serial Data Output |
| GND | Ground |
| VCC | Power Supply |
| \overline{WP} | Write Protect |
| \overline{HOLD} | Suspends Serial Input |

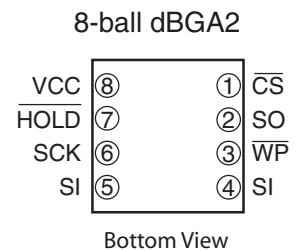
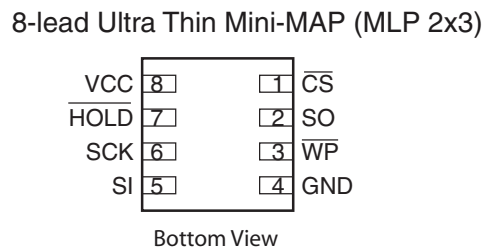
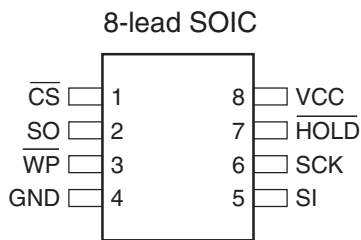


SPI Serial EEPROMs 8K (1024 x 8) 16K (2048 x 8)

**AT25080B
AT25160B**

Preliminary





Block write protection is enabled by programming the status register with one of four blocks of write protection. Separate program enable and program disable instructions are provided for additional data protection. Hardware data protection is provided via the \overline{WP} pin to protect against inadvertent write attempts to the status register. The \overline{HOLD} pin may be used to suspend any serial communication without resetting the serial sequence.

Absolute Maximum Ratings*

| | |
|--|-----------------|
| Operating Temperature..... | -55°C to +125°C |
| Storage Temperature | -65°C to +150°C |
| Voltage on Any Pin with Respect to Ground | -1.0V to +7.0V |
| Maximum Operating Voltage | 6.25V |
| DC Output Current..... | 5.0 mA |

***NOTICE:** Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Figure 0-1. Block Diagram

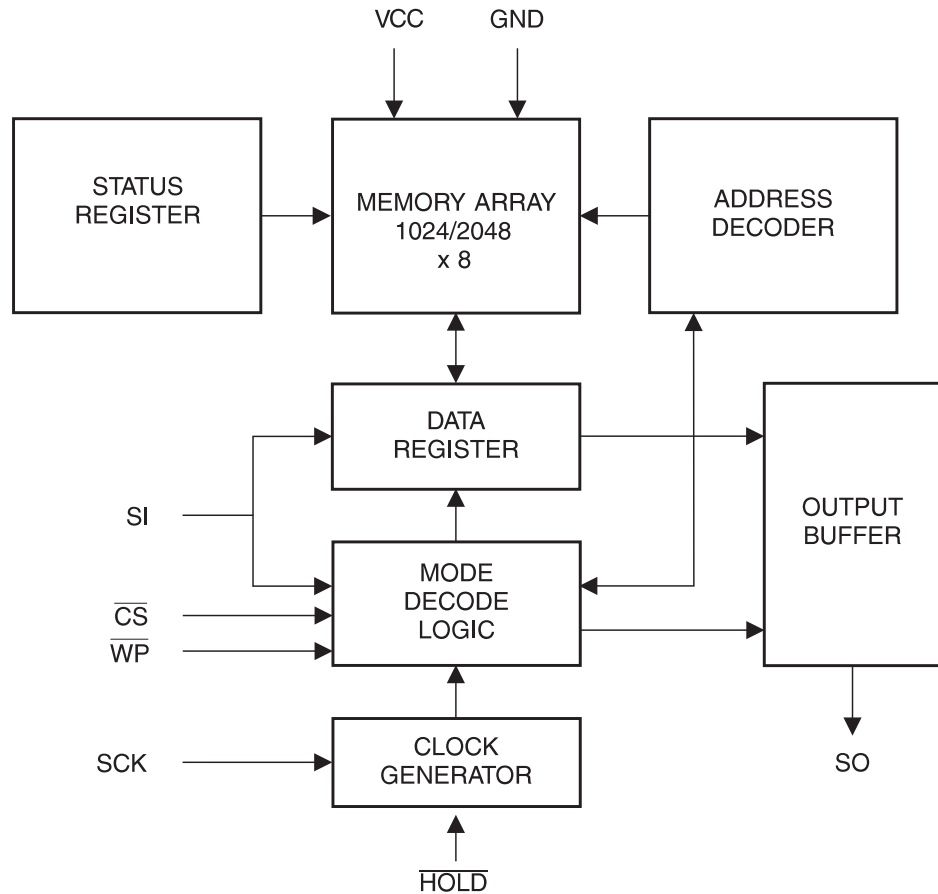


Table 0-2. Pin Capacitance⁽¹⁾

Applicable over recommended operating range from $T_A = 25^\circ\text{C}$, $f = 1.0\text{ MHz}$, $V_{CC} = +5.0\text{V}$ (unless otherwise noted)

| Symbol | Test Conditions | Max | Units | Conditions |
|-----------|--|-----|-------|-----------------------|
| C_{OUT} | Output Capacitance (SO) | 8 | pF | $V_{OUT} = 0\text{V}$ |
| C_{IN} | Input Capacitance (\overline{CS} , SCK, SI, \overline{WP} , HOLD) | 6 | pF | $V_{IN} = 0\text{V}$ |

Note: 1. This parameter is characterized and is not 100% tested.

Table 0-3. DC Characteristics

Applicable over recommended operating range from: $T_{AI} = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{CC} = +1.8\text{V}$ to $+5.5\text{V}$ (unless otherwise noted)

| Symbol | Parameter | Test Condition | Min | Typ | Max | Units |
|-----------|----------------|--|-----|-----|------|-------|
| V_{CC1} | Supply Voltage | | 1.8 | | 5.5 | V |
| V_{CC2} | Supply Voltage | | 2.7 | | 5.5 | V |
| V_{CC3} | Supply Voltage | | 4.5 | | 5.5 | V |
| I_{CC1} | Supply Current | $V_{CC} = 5.0\text{V}$ at 20 MHz, SO = Open, Read | | 7.5 | 10.0 | mA |
| I_{CC2} | Supply Current | $V_{CC} = 5.0\text{V}$ at 20 MHz, SO = Open, Read, Write | | 4.0 | 10.0 | mA |

Applicable over recommended operating range from: $T_{AI} = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{CC} = +1.8\text{V}$ to $+5.5\text{V}$ (unless otherwise noted)

| Symbol | Parameter | Test Condition | Min | Typ | Max | Units |
|----------------|---------------------|---|------------------------------------|-------|---------------------|---------------|
| I_{CC3} | Supply Current | $V_{CC} = 5.0\text{V}$ at 5 MHz, SO = Open, Read, Write | | 4.0 | 6.0 | mA |
| I_{SB1} | Standby Current | $V_{CC} = 1.8\text{V}$, $\overline{CS} = V_{CC}$ | | < 0.1 | $6.0^{(2)}$ | μA |
| I_{SB2} | Standby Current | $V_{CC} = 2.7\text{V}$, $\overline{CS} = V_{CC}$ | | 0.3 | $7.0^{(2)}$ | μA |
| I_{SB3} | Standby Current | $V_{CC} = 5.0\text{V}$, $\overline{CS} = V_{CC}$ | | 2.0 | $10.0^{(2)}$ | μA |
| I_{IL} | Input Leakage | $V_{IN} = 0\text{V}$ to V_{CC} | -3.0 | | 3.0 | μA |
| I_{OL} | Output Leakage | $V_{IN} = 0\text{V}$ to V_{CC} , $T_{AC} = 0^{\circ}\text{C}$ to 70°C | -3.0 | | 3.0 | μA |
| $V_{IL}^{(1)}$ | Input Low-voltage | | -0.6 | | $V_{CC} \times 0.3$ | V |
| $V_{IH}^{(1)}$ | Input High-voltage | | $V_{CC} \times 0.7$ | | $V_{CC} + 0.5$ | V |
| V_{OL1} | Output Low-voltage | $4.5\text{V} \leq V_{CC} \leq 5.5\text{V}$ | $I_{OL} = 3.0\text{ mA}$ | | 0.4 | V |
| V_{OH1} | Output High-voltage | | $I_{OH} = -1.6\text{ mA}$ | | $V_{CC} - 0.8$ | V |
| V_{OL2} | Output Low-voltage | $1.8\text{V} \leq V_{CC} \leq 3.6\text{V}$ | $I_{OL} = 0.15\text{ mA}$ | | 0.2 | V |
| V_{OH2} | Output High-voltage | | $I_{OH} = -100\text{ }\mu\text{A}$ | | $V_{CC} - 0.2$ | V |

Notes: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

2. Worst case measured at 85°C

Table 0-4. AC Characteristics

Applicable over recommended operating range from $T_{AI} = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{CC} = \text{As Specified}$,
CL = 1 TTL Gate and 30 pF (unless otherwise noted)

| Symbol | Parameter | Voltage | Min | Max | Units |
|-----------|------------------------------|-------------------------------|-----------------|----------------|---------------|
| f_{SCK} | SCK Clock Frequency | 4.5–5.5 2.7–5.5 1.8–5.5 | 0 0 0 | 20 10 5 | MHz |
| t_{RI} | Input Rise Time | 4.5–5.5 2.7–5.5 1.8–5.5 | | 2 2 2 | μs |
| t_{FI} | Input Fall Time | 4.5–5.5 2.7–5.5 1.8–5.5 | | 2 2 2 | μs |
| t_{WH} | SCK High Time | 4.5–5.5 2.7–5.5 1.8–5.5 | 20 40 80 | | ns |
| t_{WL} | SCK Low Time | 4.5–5.5 2.7–5.5 1.8–5.5 | 20 40 80 | | ns |
| t_{CS} | \overline{CS} High Time | 4.5–5.5 2.7–5.5 1.8–5.5 | 25 50 100 | | ns |
| t_{CSS} | \overline{CS} Setup Time | 4.5–5.5 2.7–5.5 1.8–5.5 | 25 50 100 | | ns |
| t_{CSH} | \overline{CS} Hold Time | 4.5–5.5 2.7–5.5 1.8–5.5 | 25 50 100 | | ns |
| t_{SU} | Data In Setup Time | 4.5–5.5 2.7–5.5 1.8–5.5 | 5 10 20 | | ns |
| t_{H} | Data In Hold Time | 4.5–5.5 2.7–5.5 1.8–5.5 | 5 10 20 | | ns |
| t_{HD} | \overline{HOLD} Setup Time | 4.5–5.5 2.7–5.5 1.8–5.5 | 5 10 20 | | |
| t_{CD} | \overline{HOLD} Hold Time | 4.5–5.5 2.7–5.5 1.8–5.5 | 5 10 20 | | ns |
| t_V | Output Valid | 4.5–5.5 2.7–5.5 1.8–5.5 | 0 0 0 | 20 40 80 | ns |
| t_{HO} | Output Hold Time | 4.5–5.5 2.7–5.5 1.8–5.5 | 0 0 0 | | ns |

Table 0-4. AC Characteristics (Continued)

Applicable over recommended operating range from $T_{AI} = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{CC} = \text{As Specified}$,
CL = 1 TTL Gate and 30 pF (unless otherwise noted)

| Symbol | Parameter | Voltage | Min | Max | Units |
|--------------------------|---|-------------------------------|-------------|-----------------|--------------|
| t_{LZ} | $\overline{\text{HOLD}}$ to Output Low Z | 4.5–5.5 2.7–5.5 1.8–5.5 | 0 0 0 | 25 50 100 | ns |
| t_{HZ} | $\overline{\text{HOLD}}$ to Output High Z | 4.5–5.5 2.7–5.5 1.8–5.5 | | 40 80 200 | ns |
| t_{DIS} | Output Disable Time | 4.5–5.5 2.7–5.5 1.8–5.5 | | 40 80 200 | ns |
| t_{WC} | Write Cycle Time | 4.5–5.5 2.7–5.5 1.8–5.5 | | 5 5 5 | ms |
| Endurance ⁽¹⁾ | 3.3V, 25°C, Page Mode | | 1M | | Write Cycles |

Note: 1. This parameter is characterized and is not 100% tested.

1. Serial Interface Description

MASTER: The device that generates the serial clock.

SLAVE: Because the Serial Clock pin (SCK) is always an input, the AT25080B/160B always operates as a slave.

TRANSMITTER/RECEIVER: The AT25080B/160B has separate pins designated for data transmission (SO) and reception (SI).

MSB: The Most Significant Bit (MSB) is the first bit transmitted and received.

SERIAL OP-CODE: After the device is selected with $\overline{\text{CS}}$ going low, the first byte will be received. This byte contains the op-code that defines the operations to be performed.

INVALID OP-CODE: If an invalid op-code is received, no data will be shifted into the AT25080B/160B, and the serial output pin (SO) will remain in a high impedance state until the falling edge of $\overline{\text{CS}}$ is detected again. This will reinitialize the serial communication.

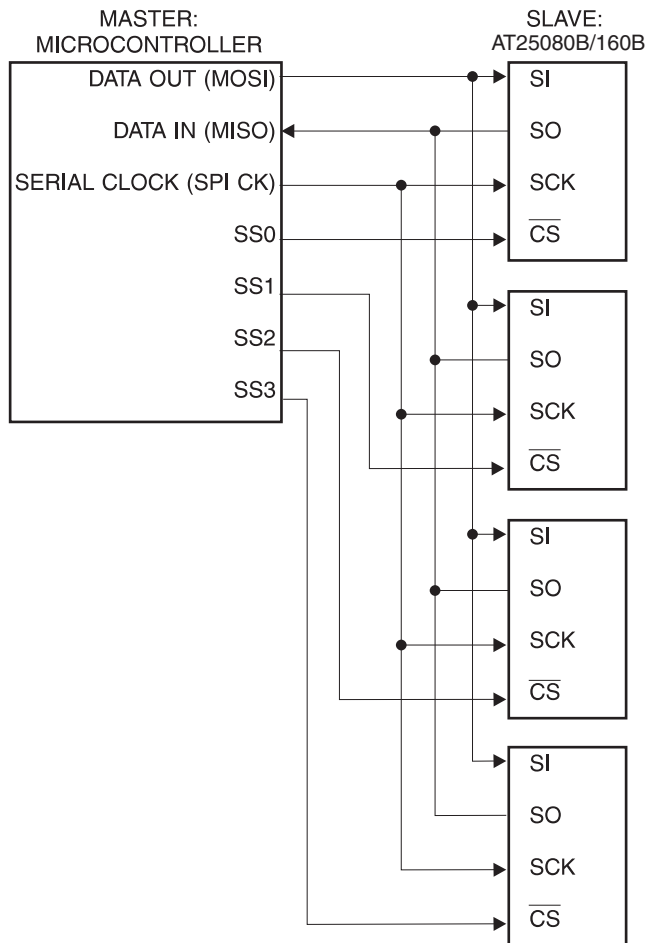
CHIP SELECT: The AT25080B/160B is selected when the $\overline{\text{CS}}$ pin is low. When the device is not selected, data will not be accepted via the SI pin, and the serial output pin (SO) will remain in a high impedance state.

HOLD: The $\overline{\text{HOLD}}$ pin is used in conjunction with the $\overline{\text{CS}}$ pin to select the AT25080B/160B. When the device is selected and a serial sequence is underway, $\overline{\text{HOLD}}$ can be used to pause the serial communication with the master device without resetting the serial sequence. To pause, the $\overline{\text{HOLD}}$ pin must be brought low while the SCK pin is low. To resume serial communication, the $\overline{\text{HOLD}}$ pin is brought high while the SCK pin is low (SCK may still toggle during $\overline{\text{HOLD}}$). Inputs to the SI pin will be ignored while the SO pin is in the high impedance state.

WRITE PROTECT: The write protect pin ($\overline{\text{WP}}$) will allow normal read/write operations when held high. When the WP pin is brought low and WPEN bit is “1”, all write operations to the status register are inhibited. $\overline{\text{WP}}$ going low while $\overline{\text{CS}}$ is still low will interrupt a write to the status register. If the internal write cycle has already been initiated, $\overline{\text{WP}}$ going low will have no effect on any write

operation to the status register. The \overline{WP} pin function is blocked when the WPEN bit in the status register is “0”. This will allow the user to install the AT25080B/160B in a system with the \overline{WP} pin tied to ground and still be able to write to the status register. All \overline{WP} pin functions are enabled when the WPEN bit is set to “1”.

Figure 1-1. SPI Serial Interface



2. Functional Description

The AT25080B/160B is designed to interface directly with the synchronous serial peripheral interface (SPI) of the 6805 and 68HC11 series of microcontrollers.

The AT25080B/160B utilizes an 8-bit instruction register. The list of instructions and their operation codes are contained in [Table 2-1](#). All instructions, addresses, and data are transferred with the MSB first and start with a high-to-low CS transition.

Table 2-1. Instruction Set for the AT25080B/160B

| Instruction Name | Instruction Format | Operation |
|------------------|--------------------|--------------------------|
| WREN | 0000 X110 | Set Write Enable Latch |
| WRDI | 0000 X100 | Reset Write Enable Latch |
| RDSR | 0000 X101 | Read Status Register |

Table 2-1. Instruction Set for the AT25080B/160B

| Instruction Name | Instruction Format | Operation |
|------------------|--------------------|-----------------------------|
| WRSR | 0000 X001 | Write Status Register |
| READ | 0000 X011 | Read Data from Memory Array |
| WRITE | 0000 X010 | Write Data to Memory Array |

WRITE ENABLE (WREN): The device will power up in the write disable state when V_{CC} is applied. All programming instructions must therefore be preceded by a Write Enable instruction.

WRITE DISABLE (WRDI): To protect the device against inadvertent writes, the Write Disable instruction disables all programming modes. The WRDI instruction is independent of the status of the \overline{WP} pin.

READ STATUS REGISTER (RDSR): The Read Status Register instruction provides access to the status register. The READY/BUSY and Write Enable status of the device can be determined by the RDSR instruction. Similarly, the Block Write Protection Bits indicate the extent of protection employed. These bits are set by using the WRSR instruction.

Table 2-2. Status Register Format

| Bit 7 | Bit 6 | Bit 5 | Bit 4 | Bit 3 | Bit 2 | Bit 1 | Bit 0 |
|-------|-------|-------|-------|-------|-------|-------|------------------|
| WPEN | X | X | X | BP1 | BP0 | WEN | \overline{RDY} |

Table 2-3. Read Status Register Bit Definition

| Bit | Definition |
|--|---|
| Bit 0 (\overline{RDY}) | Bit 0 = "0" (\overline{RDY}) indicates the device is READY. Bit 0 = "1" indicates the write cycle is in progress. |
| Bit 1 (WEN) | Bit 1 = "0" indicates the device is not WRITE ENABLED. Bit 1 = "1" indicates the device is write enabled. |
| Bit 2 (BP0) | See Table 2-4 on page 9 . |
| Bit 3 (BP1) | See Table 2-4 on page 9 . |
| Bits 4–6 are "0"s when device is not in an internal write cycle. | |
| Bit 7 (WPEN) | See Table 2-5 on page 9 . |
| Bits 0–7 are "1"s during an internal write cycle. | |

WRITE STATUS REGISTER (WRSR): The WRSR instruction allows the user to select one of four levels of protection. The AT25080B/160B is divided into four array segments. One-quarter, one-half, or all of the memory segments can be protected. Any of the data within any selected segment will therefore be read only. The block write protection levels and corresponding status register control bits are shown in [Table 2-4](#).

The three bits BP0, BP1, and WPEN are nonvolatile cells that have the same properties and functions as the regular memory cells (e.g., WREN, t_{WC} , RDSR).

Table 2-4. Block Write Protect Bits

| Level | Status Register Bits | | Array Addresses Protected | |
|--------|----------------------|-----|---------------------------|-----------|
| | BP1 | BP0 | AT25080B | AT25160B |
| 0 | 0 | 0 | None | None |
| 1(1/4) | 0 | 1 | 0300–03FF | 0600–07FF |
| 2(1/2) | 1 | 0 | 0200–03FF | 0400–07FF |
| 3(All) | 1 | 1 | 0000–03FF | 0000–07FF |

The WRSR instruction also allows the user to enable or disable the write protect (\overline{WP}) pin through the use of the Write Protect Enable (WPEN) bit. Hardware write protection is enabled when the \overline{WP} pin is low and the WPEN bit is “1”. Hardware write protection is disabled when either the \overline{WP} pin is high or the WPEN bit is “0”. When the device is hardware write protected, writes to the status register, including the block protect bits and the WPEN bit, and the block-protected sections in the memory array are disabled. Writes are only allowed to sections of the memory that are not block-protected.

NOTE: When the WPEN bit is hardware write protected, it cannot be changed back to “0” as long as the \overline{WP} pin is held low.

Table 2-5. WPEN Operation

| WPEN | \overline{WP} | WEN | Protected Blocks | Unprotected Blocks | Status Register |
|------|-----------------|-----|------------------|--------------------|-----------------|
| 0 | X | 0 | Protected | Protected | Protected |
| 0 | X | 1 | Protected | Writeable | Writeable |
| 1 | Low | 0 | Protected | Protected | Protected |
| 1 | Low | 1 | Protected | Writeable | Protected |
| X | High | 0 | Protected | Protected | Protected |
| X | High | 1 | Protected | Writeable | Writeable |

READ SEQUENCE (READ): Reading the AT25080B/160B via the Serial Output (SO) pin requires the following sequence. After the \overline{CS} line is pulled low to select a device, the read opcode is transmitted via the SI line followed by the byte address to be read (A15–A0, see [Table 2-6](#)). Upon completion, any data on the SI line will be ignored. The data (D7–D0) at the specified address is then shifted out onto the SO line. If only one byte is to be read, the \overline{CS} line should be driven high after the data comes out. The read sequence can be continued since the byte address is automatically incremented and data will continue to be shifted out. When the highest address is reached, the address counter will roll over to the lowest address allowing the entire memory to be read in one continuous read cycle.

WRITE SEQUENCE (WRITE): In order to program the AT25080B/160B, two separate instructions must be executed. First, the device **must be write enabled** via the WREN instruction. Then a write (WRITE) instruction may be executed. Also, the address of the memory location(s) to be programmed must be outside the protected address field location selected by the block write protection level. During an internal write cycle, all commands will be ignored except the RDSR instruction.

A write instruction requires the following sequence. After the \overline{CS} line is pulled low to select the device, the WRITE op-code is transmitted via the SI line followed by the byte address (A15–A0) and the data (D7–D0) to be programmed (see Table 2-6). Programming will start after the \overline{CS} pin is brought high. The low-to-high transition of the \overline{CS} pin must occur during the SCK low-time immediately after clocking in the D0 (LSB) data bit.

The READY/BUSY status of the device can be determined by initiating a read status register (RDSR) instruction. If Bit 0 = “1”, the write cycle is still in progress. If Bit 0 = “0”, the write cycle has ended. Only the RDSR instruction is enabled during the write programming cycle.

The AT25080B/160B is capable of a 32-byte page write operation. After each byte of data is received, the five low-order address bits are internally incremented by one; the high-order bits of the address will remain constant. If more than 32 bytes of data are transmitted, the address counter will roll over and the previously written data will be overwritten. The AT25080B/160B is automatically returned to the write disable state at the completion of a write cycle.

NOTE: If the device is not write-enabled (WREN), the device will ignore the write instruction and will return to the standby state, when \overline{CS} is brought high. A new \overline{CS} falling edge is required to reinitiate the serial communication.

Table 2-6. Address Key

| Address | AT25080B | AT25160B |
|-----------------|-----------------|-----------------|
| A_N | A_9-A_0 | $A_{10}-A_0$ |
| Don't Care Bits | $A_{15}-A_{10}$ | $A_{15}-A_{11}$ |

3. Timing Diagrams

Figure 3-1. Synchronous Data Timing (for Mode 0)

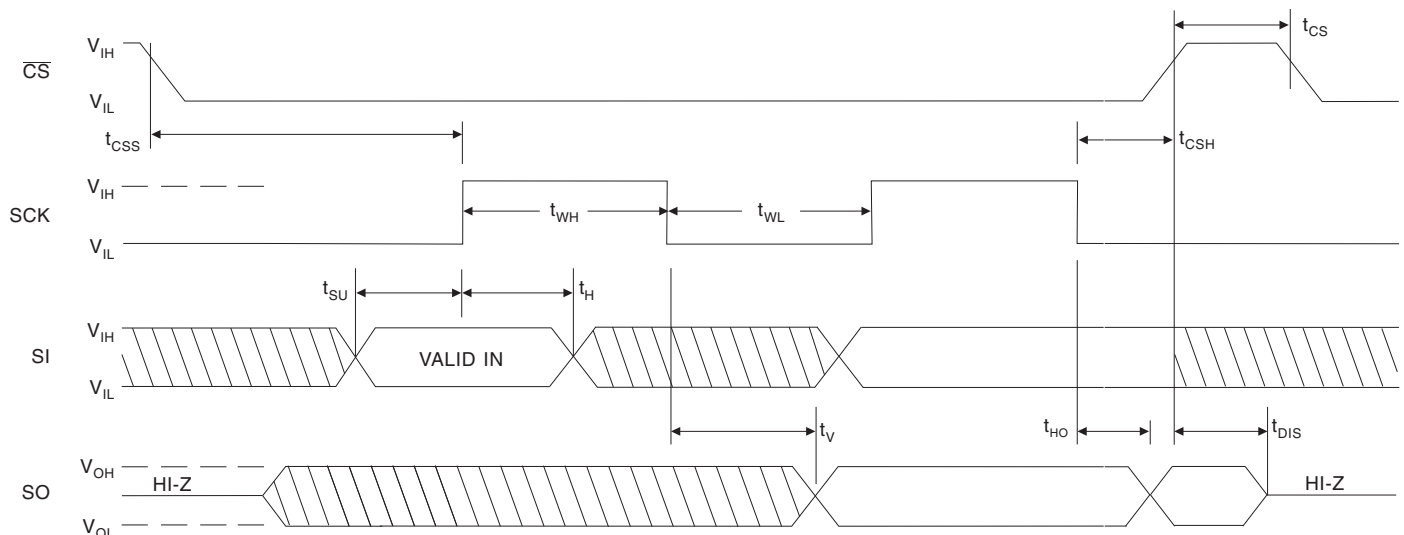


Figure 3-2. WREN Timing

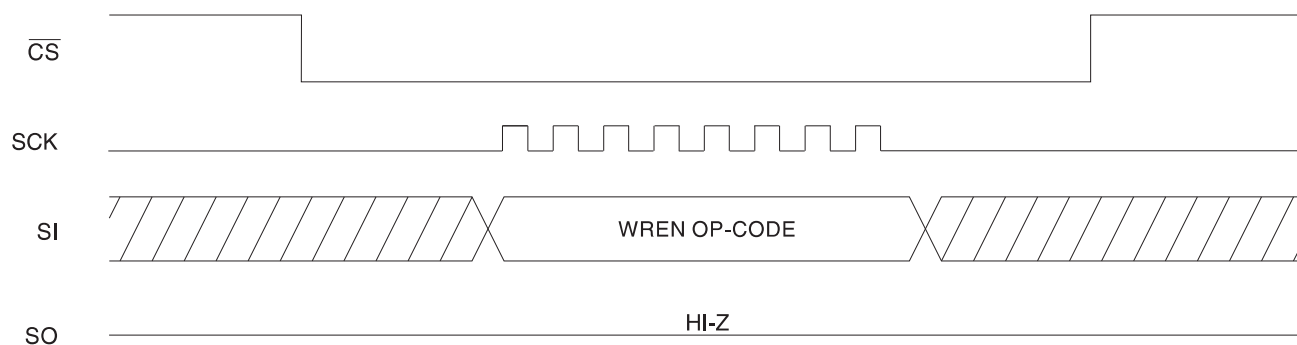


Figure 3-3. WRDI Timing

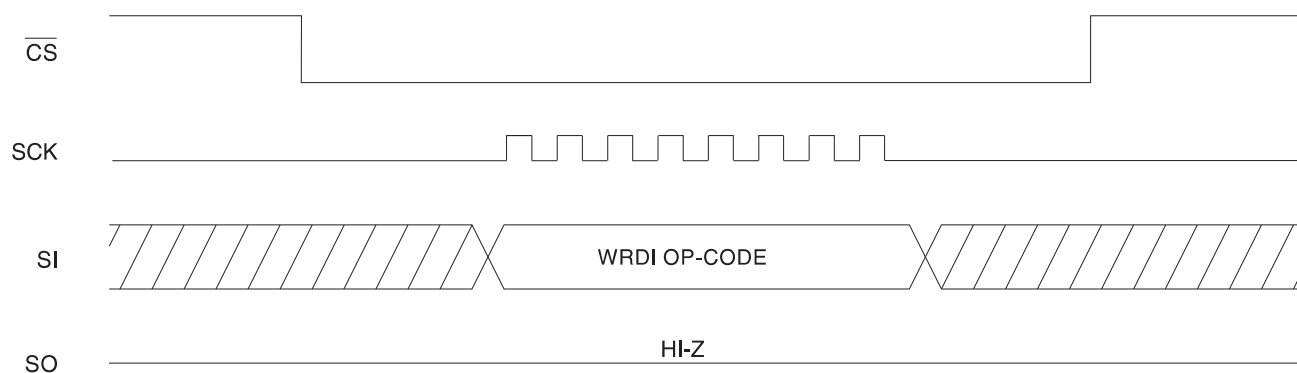


Figure 3-4. RDSR Timing

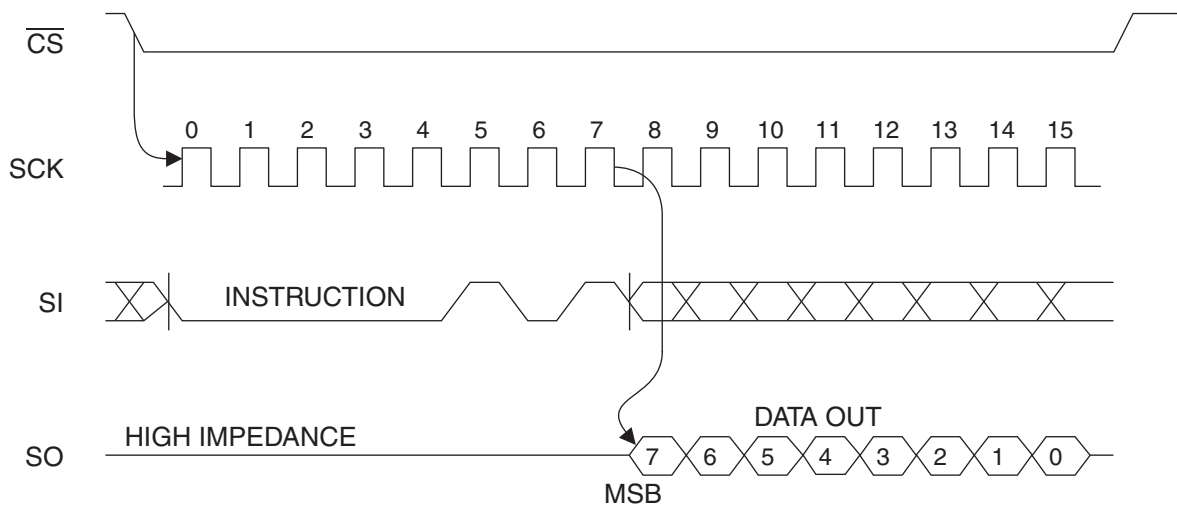


Figure 3-5. WRSR Timing

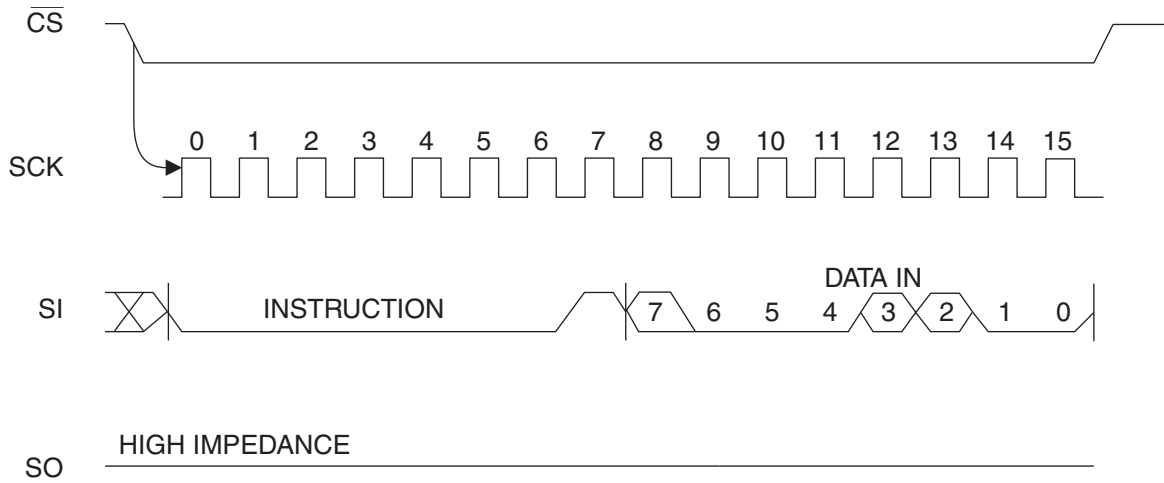


Figure 3-6. READ Timing

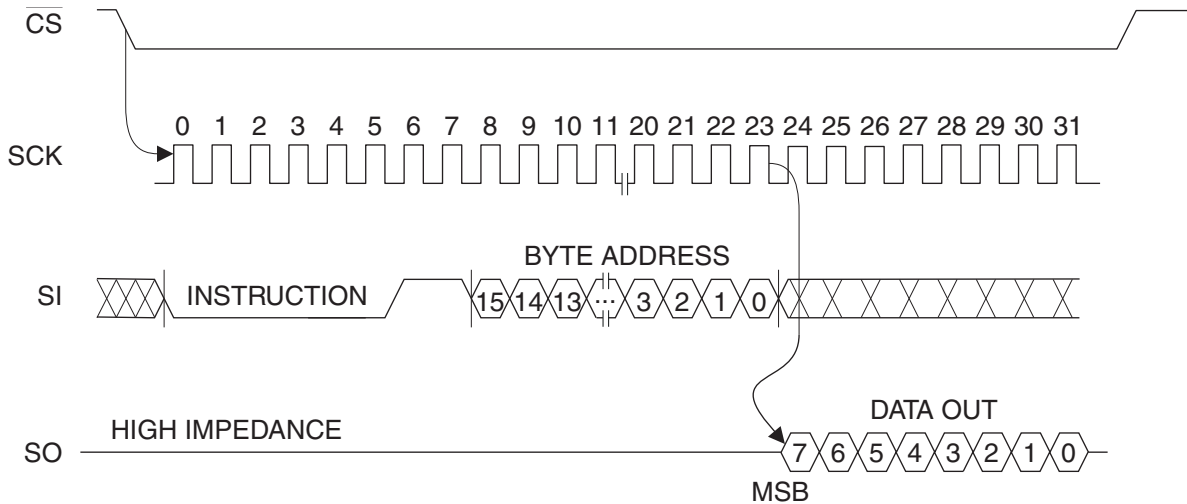


Figure 3-7. WRITE Timing

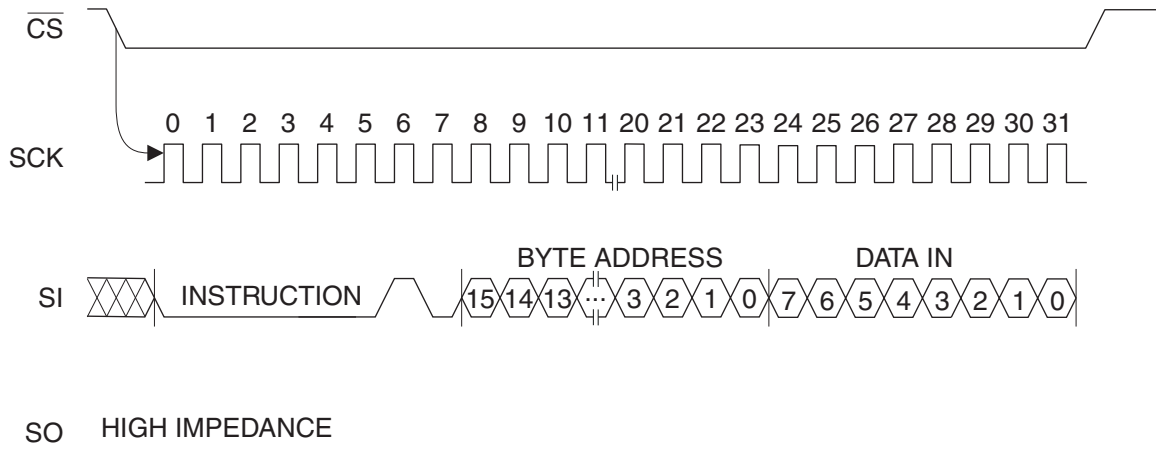
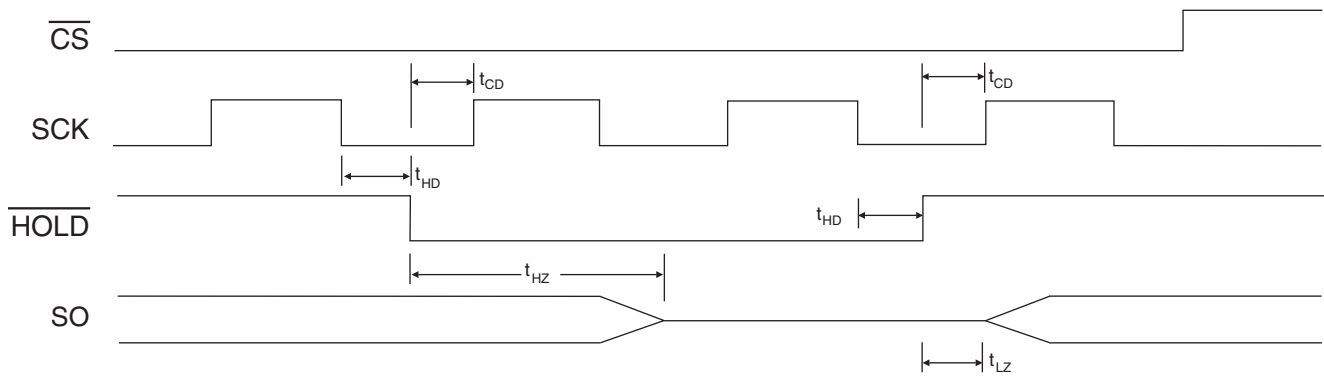


Figure 3-8. $\overline{\text{HOLD}}$ Timing



4. AT25080B Ordering Information

| Ordering Code | Voltage | Package | Operation Range |
|---|---------|----------|--|
| AT25080B-PU (Bulk form only) | 1.8 | 8P3 | Lead-free/Halogen-free/ Industrial Temperature (–40 to 85°C) |
| AT25080BN-SH-B ⁽¹⁾ (NiPdAu Lead Finish) | 1.8 | 8S1 | |
| AT25080BN-SH-T ⁽²⁾ (NiPdAu Lead Finish) | 1.8 | 8S1 | |
| AT25080B-TH-B ⁽¹⁾ (NiPdAu Lead Finish) | 1.8 | 8A2 | |
| AT25080B-TH-T ⁽²⁾ (NiPdAu Lead Finish) | 1.8 | 8A2 | |
| AT25080BY6-YH-T ⁽²⁾ (NiPdAu Lead Finish) | 1.8 | 8Y6 | |
| AT25080BD3-DH-T ⁽²⁾ | 1.8 | 8D3 | |
| AT25080BU3-UU-T ⁽²⁾ | 1.8 | 8U3-1 | Industrial Temperature (–40 to 85°C) |
| AT25080B-W-11 ⁽³⁾ | 1.8 | Die Sale | |

- Notes:
1. “B” denotes bulk.
 2. “-T” denotes tape and reel. SOIC = 4K per reel. TSSOP, Ultra Thin Mini-MAP, SOT23, and dBGA2 = 5K per reel.
 3. Available in waffle pack, tape and reel, and wafer form; order as SL788 for inkless wafer form. Bumped die available upon request. Please contact Serial Interface Marketing.

| Package Type | |
|--------------|--|
| 8P3 | 8-lead, 0.300” Wide, Plastic Dual Inline Package (PDIP) |
| 8S1 | 8-lead, 0.150” Wide, Plastic Gull Wing Small Outline (JEDEC SOIC) |
| 8A2 | 8-lead, 4.4 mm Body, Plastic Thin Shrink Small Outline Package (TSSOP) |
| 8Y6 | 8-lead, 2.00 mm x 3.00 mm Body, 0.50 mm Pitch, Ultra Thin Mini-MAP, Dual No Lead Package (DFN), (MLP 2x3 mm) |
| 8D3 | 8-lead, 1.8 mm x 2.2 mm Body, Ultra axLanda Grid Array (ULLGA) |
| 8U3-1 | 8-ball, die Ball Grid Array Package (dBGA2) |
| Options | |
| –1.8 | Low Voltage (1.8 to 5.5V) |

5. AT25160B Ordering Information

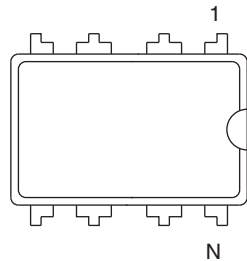
| Ordering Code | Voltage | Package | Operation Range |
|---|---------|----------|--|
| AT25160B-PU (Bulk form only) | 1.8 | 8P3 | Lead-free/Halogen-free/ Industrial Temperature (–40 to 85°C) |
| AT25160BN-SH-B ⁽¹⁾ (NiPdAu Lead Finish) | 1.8 | 8S1 | |
| AT25160BN-SH-T ⁽²⁾ (NiPdAu Lead Finish) | 1.8 | 8S1 | |
| AT25160B-TH-B ⁽¹⁾ (NiPdAu Lead Finish) | 1.8 | 8A2 | |
| AT25160B-TH-T ⁽²⁾ (NiPdAu Lead Finish) | 1.8 | 8A2 | |
| AT25160BY6-YH-T ⁽²⁾ (NiPdAu Lead Finish) | 1.8 | 8Y6 | |
| AT25160BD3-DH-T ⁽²⁾ | 1.8 | 8D3 | |
| AT25160BU3-UU-T ⁽²⁾ | 1.8 | 8U3-1 | Industrial Temperature (–40 to 85°C) |
| AT25160B-W-11 ⁽³⁾ | 1.8 | Die Sale | |

- Notes:
1. “B” denotes bulk.
 2. “-T” denotes tape and reel. SOIC = 4K per reel. TSSOP, Ultra Thin Mini-MAP, SOT23, and dBGA2 = 5K per reel.
 3. Available in tape and reel and wafer form; order as SL788 for inkless wafer form. Bumped die available upon request. Please contact Serial Interface Marketing.

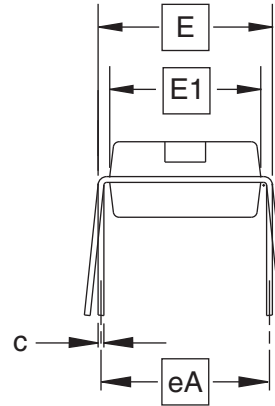
| Package Type | |
|--------------|---|
| 8P3 | 8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP) |
| 8S1 | 8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC) |
| 8A2 | 8-lead, 4.4 mm Body, Plastic Thin Shrink Small Outline Package (TSSOP) |
| 8Y6 | 8-lead, 2.00 mm x 3.00 mm Body, 0.50 mm Pitch, Ultra Thin Mini-MAP, Dual No Lead Package (DFN), (MLP 2x3mm) |
| 8D3 | 8-lead, 1.8 mm x 2.2 mm Body, Ultra axLanda Grid Array (ULLGA) |
| 8U3-1 | 8-ball, die Ball Grid Array Package (dBGA2) |
| Options | |
| –1.8 | Low Voltage (1.8 to 5.5V) |

6. Packaging Information

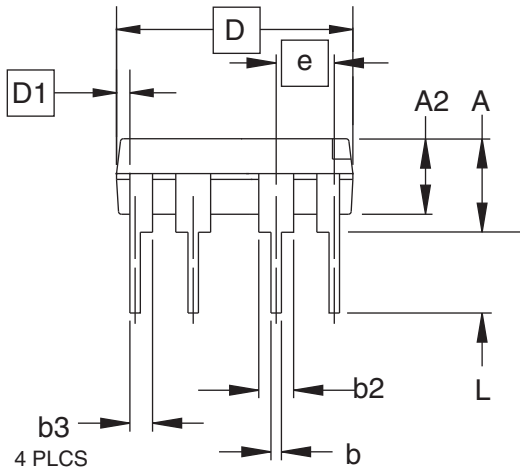
8P3 – PDIP



Top View



End View



Side View

COMMON DIMENSIONS
(Unit of Measure = inches)

| SYMBOL | MIN | NOM | MAX | NOTE |
|--------|-----------|-------|-------|------|
| A | — | — | 0.210 | 2 |
| A2 | 0.115 | 0.130 | 0.195 | |
| b | 0.014 | 0.018 | 0.022 | 5 |
| b2 | 0.045 | 0.060 | 0.070 | 6 |
| b3 | 0.030 | 0.039 | 0.045 | 6 |
| c | 0.008 | 0.010 | 0.014 | |
| D | 0.355 | 0.365 | 0.400 | 3 |
| D1 | 0.005 | — | — | 3 |
| E | 0.300 | 0.310 | 0.325 | 4 |
| E1 | 0.240 | 0.250 | 0.280 | 3 |
| e | 0.100 BSC | | | |
| eA | 0.300 BSC | | | 4 |
| L | 0.115 | 0.130 | 0.150 | 2 |

- Notes:
1. This drawing is for general information only; refer to JEDEC Drawing MS-001, Variation BA, for additional information.
 2. Dimensions A and L are measured with the package seated in JEDEC seating plane Gauge GS-3.
 3. D, D1 and E1 dimensions do not include mold Flash or protrusions. Mold Flash or protrusions shall not exceed 0.010 inch.
 4. E and eA measured with the leads constrained to be perpendicular to datum.
 5. Pointed or rounded lead tips are preferred to ease insertion.
 6. b2 and b3 maximum dimensions do not include Dambar protrusions. Dambar protrusions shall not exceed 0.010 (0.25 mm).

01/09/02



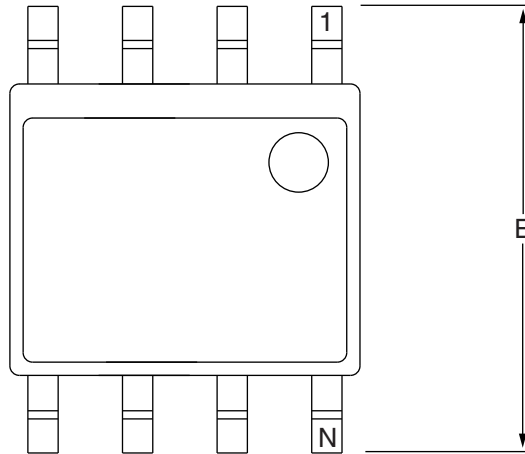
2325 Orchard Parkway
San Jose, CA 95131

TITLE
8P3, 8-lead, 0.300" Wide Body, Plastic Dual
In-line Package (PDIP)

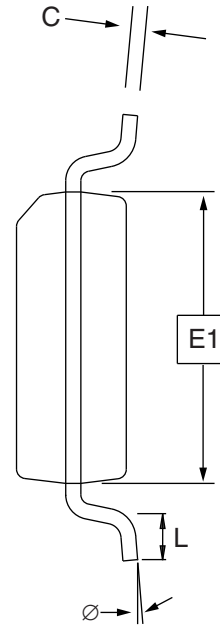
DRAWING NO.
8P3

REV.
B

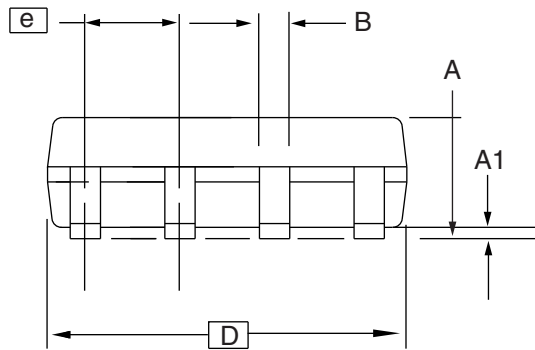
8S1 – JEDEC SOIC



Top View



End View



Side View

COMMON DIMENSIONS
(Unit of Measure = mm)

| SYMBOL | MIN | NOM | MAX | NOTE |
|--------|----------|-----|------|------|
| A | 1.35 | – | 1.75 | |
| A1 | 0.10 | – | 0.25 | |
| b | 0.31 | – | 0.51 | |
| C | 0.17 | – | 0.25 | |
| D | 4.80 | – | 5.00 | |
| E1 | 3.81 | – | 3.99 | |
| E | 5.79 | – | 6.20 | |
| e | 1.27 BSC | | | |
| L | 0.40 | – | 1.27 | |
| Ø | 0° | – | 8° | |

Note: These drawings are for general information only. Refer to JEDEC Drawing MS-012, Variation AA for proper dimensions, tolerances, datums, etc.

10/7/03



1150 E. Cheyenne Mtn. Blvd.
Colorado Springs, CO 80906

TITLE

8S1, 8-lead (0.150" Wide Body), Plastic Gull Wing
Small Outline (JEDEC SOIC)

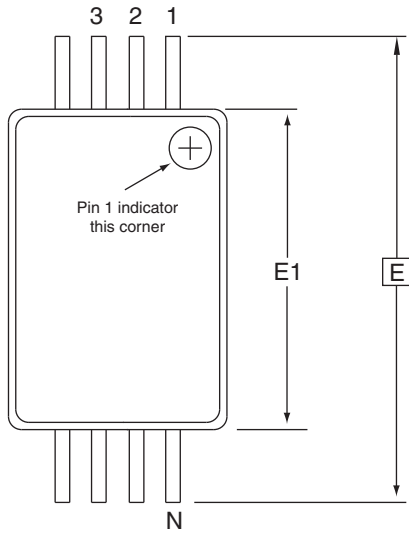
DRAWING NO.

8S1

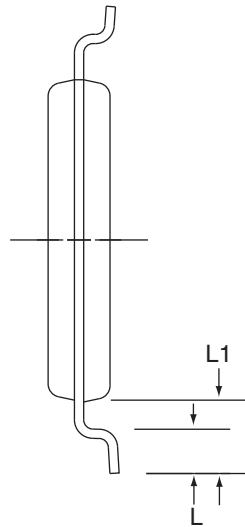
REV.

B

8A2 – TSSOP



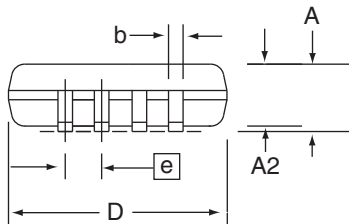
Top View



End View

COMMON DIMENSIONS (Unit of Measure = mm)

| SYMBOL | MIN | NOM | MAX | NOTE |
|--------|----------|------|------|------|
| D | 2.90 | 3.00 | 3.10 | 2, 5 |
| E | 6.40 BSC | | | |
| E1 | 4.30 | 4.40 | 4.50 | 3, 5 |
| A | – | – | 1.20 | |
| A2 | 0.80 | 1.00 | 1.05 | |
| b | 0.19 | – | 0.30 | 4 |
| e | 0.65 BSC | | | |
| L | 0.45 | 0.60 | 0.75 | |
| L1 | 1.00 REF | | | |



Side View

- Notes:
1. This drawing is for general information only. Refer to JEDEC Drawing MO-153, Variation AA, for proper dimensions, tolerances, datums, etc.
 2. Dimension D does not include mold Flash, protrusions or gate burrs. Mold Flash, protrusions and gate burrs shall not exceed 0.15 mm (0.006 in) per side.
 3. Dimension E1 does not include inter-lead Flash or protrusions. Inter-lead Flash and protrusions shall not exceed 0.25 mm (0.010 in) per side.
 4. Dimension b does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the b dimension at maximum material condition. Dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and adjacent lead is 0.07 mm.
 5. Dimension D and E1 to be determined at Datum Plane H.

5/30/02



2325 Orchard Parkway
San Jose, CA 95131

TITLE

8A2, 8-lead, 4.4 mm Body, Plastic
Thin Shrink Small Outline Package (TSSOP)

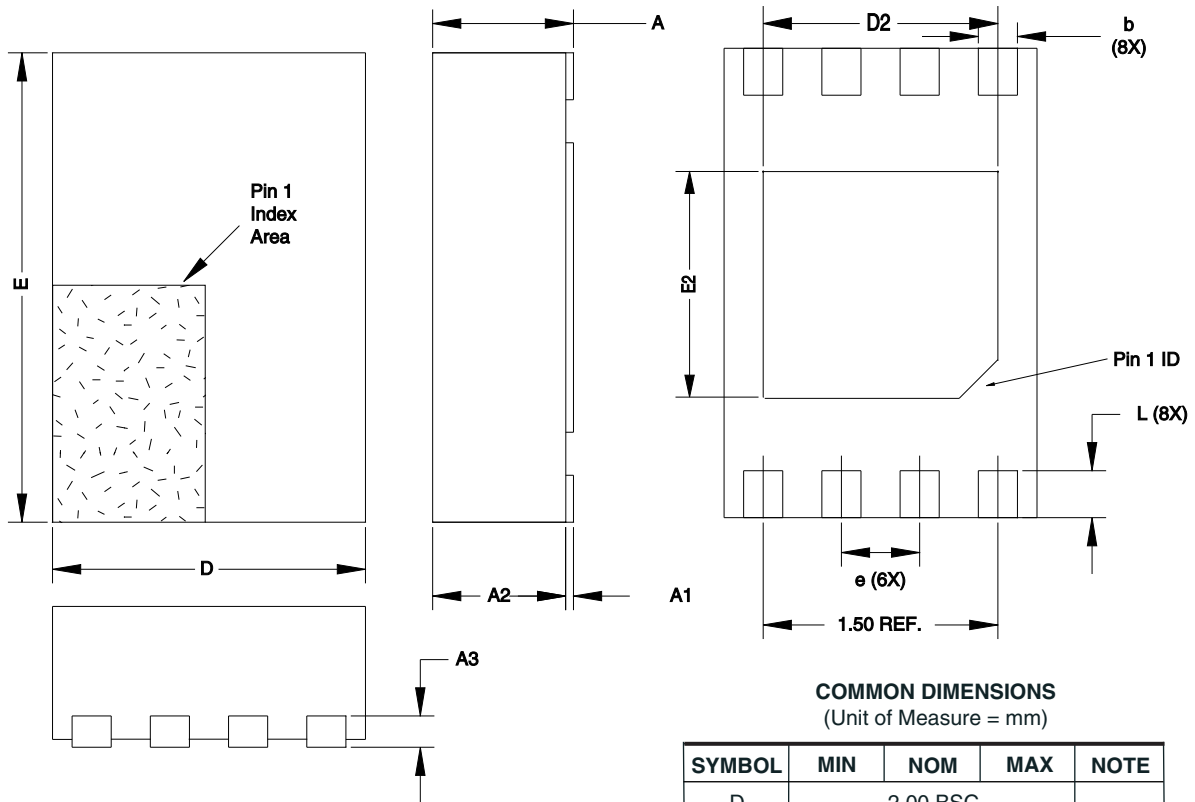
DRAWING NO.

8A2

REV.

B

8Y6 – Mini MAP



COMMON DIMENSIONS
(Unit of Measure = mm)

| SYMBOL | MIN | NOM | MAX | NOTE |
|--------|------|----------|------|------|
| D | | 2.00 BSC | | |
| E | | 3.00 BSC | | |
| D2 | 1.40 | 1.50 | 1.60 | |
| E2 | - | - | 1.40 | |
| A | - | - | 0.60 | |
| A1 | 0.0 | 0.02 | 0.05 | |
| A2 | - | - | 0.55 | |
| A3 | | 0.20 REF | | |
| L | 0.20 | 0.30 | 0.40 | |
| e | | 0.50 BSC | | |
| b | 0.20 | 0.25 | 0.30 | 2 |

- Notes:
1. This drawing is for general information only. Refer to JEDEC Drawing MO-229, for proper dimensions, tolerances, datums, etc.
 2. Dimension b applies to metallized terminal and is measured between 0.15 mm and 0.30 mm from the terminal tip. If the terminal has the optional radius on the other end of the terminal, the dimension should not be measured in that radius area.

8/26/05



2325 Orchard Parkway
San Jose, CA 95131

TITLE

8Y6, 8-lead 2.0 x 3.0 mm Body, 0.50 mm Pitch, Ultra Thin Mini-Map,
Dual No Lead Package (DFN) ,(MLP 2x3)

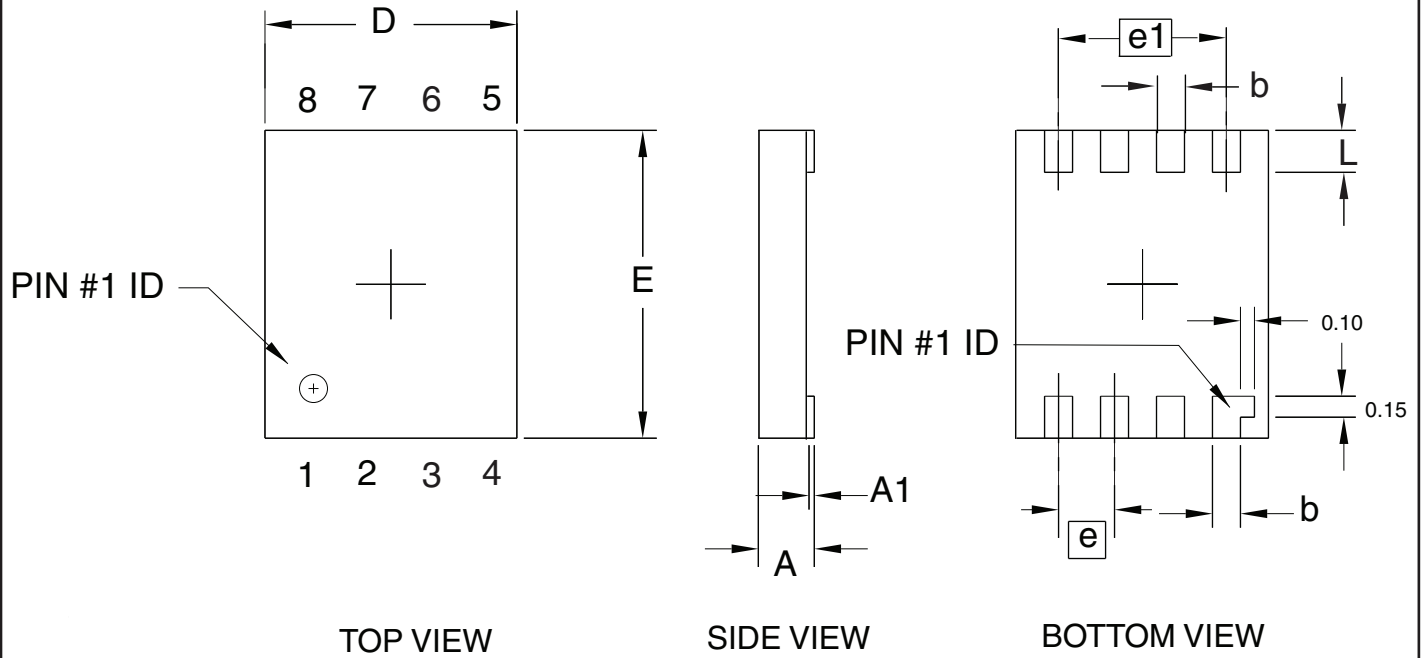
DRAWING NO.

8Y6

REV.

C

8D3 - ULLGA



COMMON DIMENSIONS
(Unit of Measure = mm)

| SYMBOL | MIN | NOM | MAX | NOTE |
|--------|------|----------|------|------|
| A | — | — | 0.40 | |
| A1 | 0.00 | — | 0.05 | |
| D | 1.70 | 1.80 | 1.90 | |
| E | 2.10 | 2.20 | 2.30 | |
| b | 0.15 | 0.20 | 0.25 | |
| e | | 0.40 TYP | | |
| e1 | | 1.20 REF | | |
| L | 0.25 | 0.30 | 0.35 | |

11/15/05



1150 E. Cheyenne Mtn. Blvd.
Colorado Springs, CO 80906

TITLE

8D3, 8-lead (1.80 x 2.20 mm Body) Ultra Leadframe
Land Grid Array (ULLGA) D3

DRAWING NO.

8D3

REV.

0

7. Revision History

| Lit No. | Date | Comments |
|---------|--------|---|
| 5228B | 7/2008 | Changed 'Endurance' parameter on page 6 |
| 5228A | 9/2007 | Initial document release. |



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